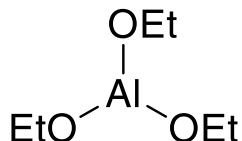


Catalog # 93-1370 Aluminum ethoxide, 99%



Thermal Behavior:

- Melting point: 140°C
- Boiling point: 320°C

Technical Notes:

1. ALD precursor for aluminum containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Zr _x Al _y O _z	ALD	-	7.5 Torr	ZrCl ₄	400°C	1
Al _x Si _y O _z	ALD	135°C	7.5 Torr	SiCl ₄ or SiMe ₄	300-500°C 200-500°C	2

References:

1. [Science 2000, 288, 319.](#)
2. [J. Electrochem. Soc. 2011, 158, P15.](#)